Messrs. Rockwell Automation

SPECIFICATION

 Device Name
 : Diode Module with Brake

 Type Name
 : 6R1MBi125LP-160-04

 Spec. No.
 : MS 5T 0 02 07

 Date
 : Nov - 17 - '03

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	DATE	NAME	APPROVED
	Nov-17-103		
CHECKED	NOV-17- 63	T. Myasola	4 Sely
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Revised Records

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Date	Classi- fication	Ind.	Content	Applied date	Drawn	Check ed	Check ed	Appro ved
Nov -17 -103	Enactment	_		Issued date		K. Gameda T. Myasila		y Sel

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Ratings and characteristics of diode module with Brake

Type: 6R1MBi125LP-160-04

1.Maxmum rating(at Tj=25°C / Tc=25°C unless otherwise specified)

Item :		Symbol	Con	dition	Max.	Unit
	Repetitive peak reverse voltage	V_{RRM}			1600	V
	Non-repetitive peak reverse voltage	v_{RSM}			1900	V
Converter	Average output current	Io	50Hz/60H Tc=103°C	Iz sine wave	125	A
)on	One cycle surge current (50Hz)	IFSM	From rate	ed load	1200	A
	I2t	I2t	From rate	ed load	6000	A^2s
	Operation junction temperature	Tj			-40 to +150	သိ
	Collector-Emitter voltage	V_{CES}			1200	V
	Gate-Emitter voltage	v_{GES}			±20	V
	Collector current	Ic	DC	Tc=25°C	110	A
ke				Tc=44°C	100	
Brake		Icp	1ms	Tc=25°C	-	A
				Tc=44°C	-	
	Collector power dissipation	Pc			280	W
	Repetitive peak reverse voltage	V_{RRM}			1400	V
	Operation junction temperature	Tj			-40 to +150	°C
Storage junction temperature		Tstg			-40 to +125	°C
Iso	lation voltage	Viso	AC:1min		3000	V
Mo	unting screw torque		M5 screw		2.0 to 2.5	N⋅m

2.electrical characteristics (at Tj=25°C / Tc=25°C unless otherwise specified)

	Item	Symbol	Condition	min.	typ.	Max.	Unit
S.	Forward voltage	V_{FM}	I _{FM} =125A	-	-	1.35	V
	Reverse current	I_{RRM}	Tj=150°C, $V_R^{=V}_{RRM}$	-	-	10.0	mA
	Zero gate voltage Collector current	ICES	V_{GE} =0V, V_{CE} =1200V	-	-	1.0	mA
	Gate-Emitter leakage current	$I_{\hbox{GES}}$	V_{CE} =0V, V_{GE} =±20V	-	-	200	nA
	Collector-Emitter saturation voltage	V _{CE(sat)}	$V_{ m GE}$ =15V, Ic=100A	-	2.10	2.45	V
Brake	Turn-on time	ton	Vcc=600V	-	0.36	1.20	
Br		tr	Ic=100A	-	0.21	0.60	us
	Turn-off time	toff	$V_{GE} = \pm 15V$	-	0.37	1.00	
		tf	$R_{G}^{=5.6}\Omega$	-	0.07	0.30	
	Reverse current	I_{RRM}	$V_R = V_{RRM}$	-	-	1.0	mA
	Forward voltage	V _{FM}	I _{FM} =35A	-	2.0	3.0	V

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3. Thermal characteristics

Item	Symbol	Condition		min.	typ.	Max.	Unit
Thermal resistance	Rth _(i-c)	Converter Per total loss		-	-	0.13	
	90		Per each device	-	-	0.78	°C/W
		Brake IGBT (1device)		-	-	0.44	
		Brake FWI	(1device)	-	-	1.50	
Thermal resistance (case to fin)	Rth _(c-f)	with thermal compound		-	0.08	-	°C/W

- 4. Outline drawing and equivalent circuit are shown in page P5/12
- 5. Applicable category

This specification is applied to Diode module with Brake named 6R1MBi125LP-160-04. This product is selection version of V_{RSM} =1900V from V_{RRM} =1600V / V_{RSM} =1760V device. All of reliability test condition at Conv-diode is also based on V_{RRM} =1600V / V_{RSM} =1760V device.

- 6. Storage and transportation notes
 - 6.1 The module should be stored at a standard temperature of 5 to 35°C and humidity of 45 to 75%
 - 6.2 Store modules in a place with few temperature changes in order to avoid condensation on the module surface.
 - 6.3 Avoid exposure to corrosive gases and dust.
 - 6.4 Avoid excessive external force on the module
 - 6.5 Store module with unprocessed terminals.
 - 6.6 Do not drop or otherwise shock the modules when transporting.

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			Relia	bility Test Items			
Test cate- gories	- Test items		Test methods and conditions		Reference norms EIAJ ED-4701 (Aug2001 edition)	Number of sample	Accept- ance number
	1	Terminal Strength (Pull test)		: 40N : 10±1 sec.	Test Method 401 Method 1	5	(1:0)
	2	Mounting Strength	Screw torque : Test time	: 2.0 ~ 2.5 N·m (M5)	Test Method 402 Method 2	5	(1:0)
ests	3	Vibration	Range of frequency : Sweeping time Acceleration Sweeping direction : E	10 ~ 500Hz : 15 min. : 10G	Test Method 403 Reference 1 Condition code B	5	(1:0)
Mechanical Tests	4	Shock	Maximum acceleration Pulse width Direction		Test Method 404 Condition code B	5	(1:0)
Me	5	Solderabitlity	Solder temp. Immersion time Test time	: 235±5 °C : 5±1sec. : 1 time be Immersed in solder	Test Method 303 Condition code A	5	(1:0)
	6	Resistance to Soldering Heat	Solder temp. Immersion time Test time	: 260±5 °C : 10±1sec. : 1 time be Immersed in solder	Test Method 302 Condition code A	5	(1:0)
	1	High Temperature Storage	Storage temp.	: 125±5 °C : 1000hr.	Test Method 201	5	(1:0)
	2	Low Temperature Storage	Storage temp.	: -40±5 °C : 1000hr.	Test Method 202	5	(1:0)
	3	Temperature Humidity Storage	Storage temp. Relative humidity	: 85±2 °C : 85±5% : 1000hr.	Test Method 103 Test code C	5	(1:0)
sts	4	Unsaturated Pressure Cooker	Test temp. Atmospheric pressure Test humidity	: 120±2°C	Test Method 103 Test code E	5	(1:0)
Environment Tests	5	Temperature Cycle	Test temp. Dwell time	: Low temp40±5°C	Test Method 105	5	(1:0)
	6	Thermal Shock	Test temp. Used liquid: Water w Dipping time Transfer time	High temp. 100 -5 °C Low temp. 0 -0 °C ith ice and boiling water 5 min. par each temp. 10 sec. 10 cycles	Test Method 307 method I Condition code A	5	(1:0)

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Reliability Test Items

Test cate- gories	Test items	Tes	Test methods and conditions			ance number
	 ligh temperature Reverse Bias	Test temp. Bias Voltage	 : Ta = 125±5°C (Ti ≤ 150 °C) : VC= 0.8×VRRM(Conv.part Di) VC= 0.8×VCES(Brake IGBT) VC= 0.8×VRRM(Brake FWD) 	Test Method 101	5	(1:0)
ıts		Bias Method	: Conv.Part Di Applied AC voltage to A-K Brake IGBT / Brake FWD Applied DC voltage to C-E / A-K VGE = 0V			
Endurance Tests	 ligh temperature Bias	Test duration Test temp. Bias Voltage Bias Method Test duration	: 1000hr. : Ta = 125±5°C (Tj ≦ 150 °C) : VC = VGE = +20V or -20V : Applied DC voltage to G-E VCE = 0V : 1000hr.	Test Method 101	5	(1:0)
	ntermitted Operating Life Power cycle) for IGBT)	ON time OFF time Test temp. Number of cycles	 : 1 sec. : 9 sec. : Δ Tj=100±5deg(visual temperature) Tj ≦ 150 °C, Ta=25±5 °C : 45,000 cycles 	Test Method 106		(1:0)
	ntermitted Operating Life Power cycle) for Conv.Di)	Test temp. Number of cycles	: ∆ Tf=60±5 deg Tj ≦ 150 °C, Tfmin≦30 °C : 5000 cycles	Test Method 106	5	(1:0)

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Failure Criteria

Item	Characte	eristic	Symbol	Failure	criteria	Unit	Note
10111	Onaraot	5110410	C y 2 01		Upper limit	• • • • • • • • • • • • • • • • • • • •	11010
	Leakage cur	rent	IRRM	_	USL×1.2	mΑ	Conv.Part Di,Tj=Tjmax
Electrical			ICES	-	USL×2	mΑ	
characteristic			±IGES	_	USL×2	μΑ	
			IRRM	-	USL×2	mΑ	
	Gate thresho	old voltage	VGE(th)	LSL×0.8	USL×1.2	mΑ	
	Saturation voltage		VCE(sat)	-	USL×1.2	٧	
	Forward volt	age	VF	-	USL×1.2	٧	Conv.Di.Brake FWD
		Conv.Di	ΔVF	-	USL×1.2	mV	
	Thermal	IGBT	ΔVGE	-	USL×1.2	mV	
	resistance		or ∆ VCE				
		FWD	Δ VF	-	USL×1.2	mV	
	Isolation volt	tage	Viso	Broken i	nsulation	-	
Visual	Visual inspe	ction					
inspection	Peeling		_	The visua	al sample	-	
	Plating						
	L and the o	thers					

LSL: Lower specified limit. USL: Upper specified limit.

Note Each parameter measurement read-outs shall be made after stabilizing the components at room ambient for 2 hours minimum, 24 hours maximum after removal from the tests. And in case of the wetting tests, for example, moisture resistance tests, each component shall be made wipe or dry completely before the measurement.

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Reliability Test Results

Test cate- gories		Test items	Reference norms EIAJ ED-4701 (Aug2001 edition)	Number of test sample	Number of failure sample
		Terminal Strength (Pull test)	Test Method 401 Method 1	5	0
sts	2	Mounting Strength	Test Method 402 Method 2	5	0
al Te	3	Vibration	Test Method 403 Condition code B	5	0
Mechanical Tests	4	Shock	Test Method 404 Condition code B	5	0
Me	5	Solderabitlity	Test Method 303 Condition code B	5	0
	6 Resistance to Soldering Heat		Test Method 302 Condition code A	5	0
	1	High Temperature Storage	Test Method 201	5	0
		Low Temperature Storage	Test Method 202	5	0
nent is		Temperature Humidity Storage	Test Method 103 Test code C	5	0
Environment Tests	4	Y	Test Method 103 Test code E	5	0
<u>ы</u>	5	Temperature Cycle	Test Method 105	5	0
		Thermal Shock	Test Method 307 method I Codition code A	5	0
	1	High temperature Reverse Bias		5	0
Fests		High temperature Bias (for gate)	Test Method 101	5	0
Endurance Tests	3	Intermitted Operating Life (Power cycling) (for IGBT)	Test Method 106	5	0
End	4	Intermitted Operating Life (Power cycling) (for Conv.Di)	Test Method 106	5	0

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Warnings

- This product shall be used within its abusolute maximun rating (voltage, current, and temperature). This product may be broken in case of using beyond the ratings.
- Conect adequate fuse or protector of circuit between three-phase line and this product to prevent the equipment from causing secondary destruction.
- Use this product after realizing enough working on environment and considering of product's reliability life.
 - This product may be broken before target life of the system in case of using beyond the product's reliability life.
- If the product had been used in the environment with acid, organic matter, and corrosive gas
 (hydrogen sulfide,sulfurous acid gas), the product's performance and appearance can not be ensured
 easily.
- Use this product within the power cycle curve (Ref,MT5T02259)
- Never add mechanical stress to deform the main or control terminal. The deformed terminal may cause poor contact probrem.
- Use this product with keeping the cooling fin's flatness between screw holes within 100um and the rouphness within 10um. Also keep the tightening torque within the limits of this specification.
 Improper handling may cause isolation breakdown and this may lead to a cirtical accident.
- It shall be confirmed that IGBT's operating locus of the turn-off voltage and current are within the RBSOA specification. This product may be broken if the locus is out of the RBSOA.
- If excessive static electricity is applied to the control terminals, the devices can be broken. Implement some countermeasures against static electricity.

Cautions

- Fuji Electric is constantly making every endeavor to improve the product quality and reliability. However, semiconductor products may rarely happen to fail or malfunction. To prevent accidents causing injuly ot death, damage to property like by fire, and other social damage resulted from a failure or malfunction of the Fuji Electric semiconductor products, take some measures to keep safety such as redundant design, spread-fire-preventive design, and malfunction-protective design.
- The application examples described in this specification only explain typical ones that used the Fuji Electric products. This specification never ensure to enforce the industrial property and other rights, nor license the enforcement rights.
- The product described in this specification is not designed nor made for being applied to the equipment or systems used under life-threatening situations. When you consider applying the product of this specification to particular used, such as vehicle-mounted units, shipboard equipment, aerospace equipment ,medical devices, atomic control systems and submarine ralaying equipment or systems, please apply after confirmation of this product to be satisfied about system construction and required reliability.

If there is any unclear matter in this specification, please contact Fuji Electric Co.,Ltd.